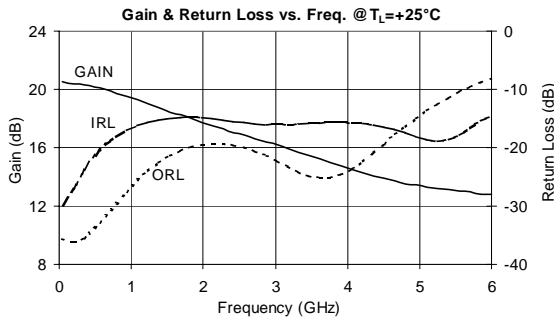


## Product Description

Sirenza Microdevices' NGA-586 is a high performance InGaP/GaAs Heterojunction Bipolar Transistor MMIC Amplifier. A Darlington configuration designed with InGaP process technology provides broadband performance up to 5.5 GHz with excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. At 850 MHz and 80mA, the NGA-586 typically provides +39.6 dBm output IP<sub>3</sub>, 19.8 dB of gain, and +18.9 dBm of 1dB compressed power using a single positive voltage supply. Only 2 DC-blocking capacitors, a bias resistor and an optional RF choke are required for operation.



## NGA-586

### DC-5.5 GHz, Cascadable InGaP/GaAs HBT MMIC Amplifier



# OBSOLETE

See Application Note AN-059 for Alternates

## Product Features

- High Gain : 18.6 dB at 1950 MHz
- Cascadable 50 Ohm
- Patented InGaP Technology
- Operates From Single Supply
- Low Thermal Resistance Package

## Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

| Symbol              | Parameter                             | Units | Frequency                       | Min. | Typ.                 | Max. |
|---------------------|---------------------------------------|-------|---------------------------------|------|----------------------|------|
| G                   | Small Signal Gain                     | dB    | 850 MHz<br>1950 MHz<br>2400 MHz | 17.8 | 19.8<br>18.6<br>17.9 | 21.8 |
| P <sub>1dB</sub>    | Output Power at 1dB Compression       | dBm   | 850 MHz<br>1950 MHz             |      | 18.9<br>18.5         |      |
| OIP <sub>3</sub>    | Output Third Order Intercept Point    | dBm   | 850 MHz<br>1950 MHz             |      | 39.6<br>34.0         |      |
| Bandwidth           | Determined by Return Loss (>10dB)     | MHz   |                                 |      | 5500                 |      |
| IRL                 | Input Return Loss                     | dB    | 1950 MHz                        |      | 14.9                 |      |
| ORL                 | Output Return Loss                    | dB    | 1950 MHz                        |      | 19.5                 |      |
| NF                  | Noise Figure                          | dB    | 1950 MHz                        |      | 3.5                  |      |
| V <sub>D</sub>      | Device Operating Voltage              | V     |                                 | 4.5  | 4.9                  | 5.4  |
| I <sub>D</sub>      | Device Operating Current              | mA    |                                 | 72   | 80                   | 88   |
| R <sub>TH</sub> J-I | Thermal Resistance (junction to lead) | °C/W  |                                 |      | 121                  |      |

### Test Conditions:

$$V_S = 8v$$

$$R_{BIAS} = 39 \text{ Ohms}$$

$$I_D = 80mA \text{ Typ.}$$

$$T_L = 25^\circ C$$

$$IP_3 \text{ Tone Spacing} = 1 \text{ MHz, } P_{out} \text{ per tone} = 0 \text{ dBm}$$

$$Z_S = Z_L = 50 \text{ Ohms}$$

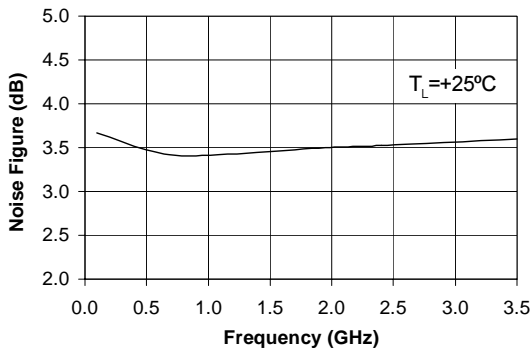
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### Typical RF Performance at Key Operating Frequencies

| Symbol           | Parameter                          | Unit | Frequency (MHz) |      |      |      |      |      |
|------------------|------------------------------------|------|-----------------|------|------|------|------|------|
|                  |                                    |      | 100             | 500  | 850  | 1950 | 2400 | 3500 |
| G                | Small Signal Gain                  | dB   | 20.5            | 20.1 | 19.8 | 18.6 | 17.9 | 15.5 |
| OIP <sub>3</sub> | Output Third Order Intercept Point | dBm  | 37.7            | 38.6 | 39.6 | 34.0 | 32.0 | 27.4 |
| P <sub>1dB</sub> | Output Power at 1dB Compression    | dBm  | 20.1            | 19.0 | 18.9 | 18.5 | 17.9 | 13.7 |
| IRL              | Input Return Loss                  | dB   | 29.3            | 21.3 | 17.7 | 14.9 | 15.4 | 15.8 |
| ORL              | Output Return Loss                 | dB   | 35.9            | 33.8 | 28.7 | 19.5 | 19.6 | 25   |
| S <sub>21</sub>  | Reverse Isolation                  | dB   | 22.7            | 22.7 | 22.6 | 22.1 | 21.9 | 21.1 |
| NF               | Noise Figure                       | dB   | 3.7             | 3.5  | 3.4  | 3.5  | 3.5  | 3.6  |

**Test Conditions:** V<sub>S</sub> = 8 V, I<sub>D</sub> = 80 mA Typ., OIP<sub>3</sub> Tone Spacing = 1 MHz, P<sub>out</sub> per tone = 0 dBm  
R<sub>BIAS</sub> = 39 Ohms, T<sub>L</sub> = 25°C, Z<sub>S</sub> = Z<sub>L</sub> = 50 Ohms

**Noise Figure vs. Frequency**  
V<sub>D</sub> = 4.9 V, I<sub>D</sub> = 80 mA



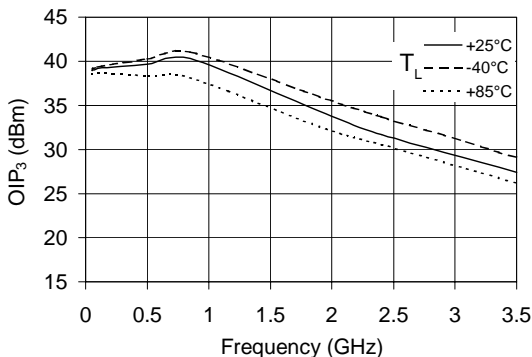
### Absolute Maximum Ratings

| Parameter                               | Absolute Limit |
|---|----------------|
| Max. Device Current (I <sub>D</sub> )   | 120 mA         |
| Max. Device Voltage (V <sub>D</sub> )   | 6 V            |
| Max. RF Input Power                     | +15 dBm        |
| Max. Junction Temp. (T <sub>J</sub> )   | +150°C         |
| Operating Temp. Range (T <sub>L</sub> ) | -40°C to +85°C |
| Max. Storage Temp.                      | +150°C         |

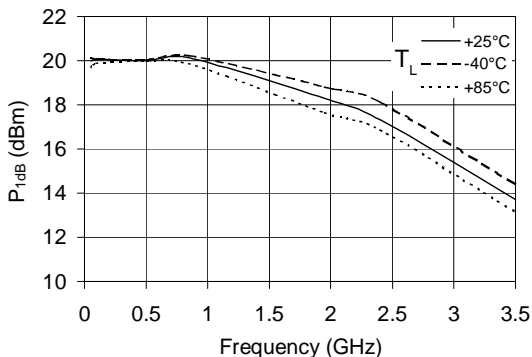
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

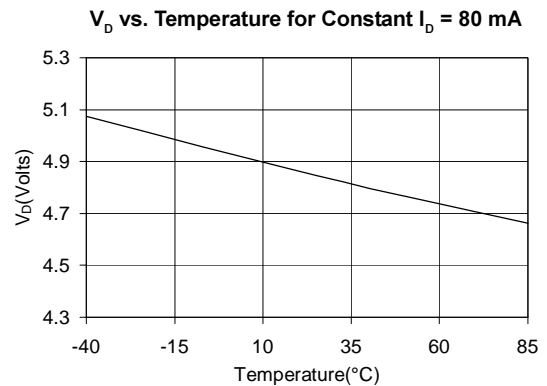
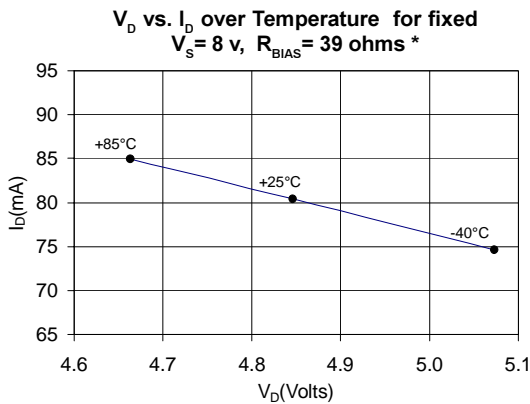
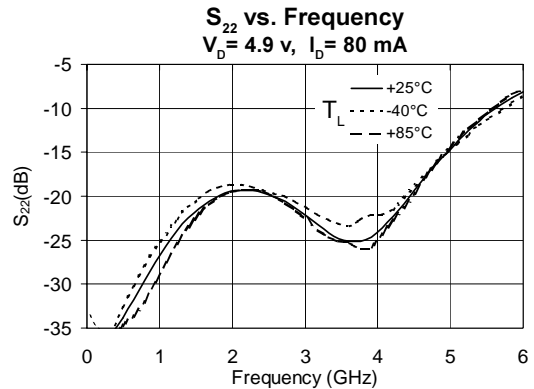
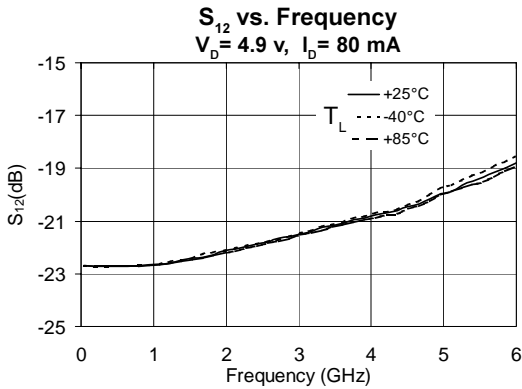
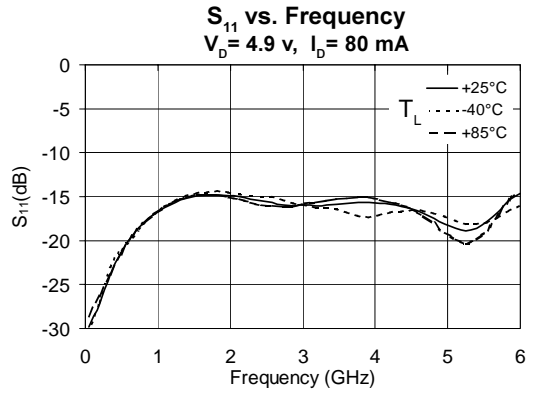
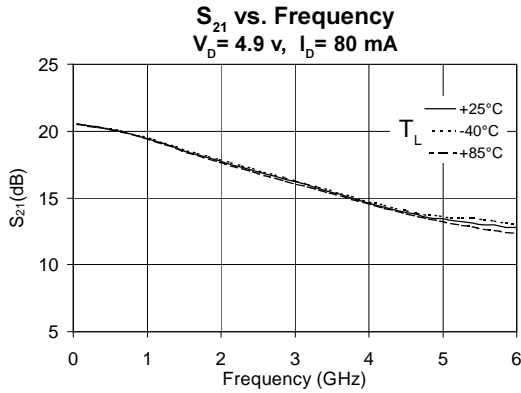
Bias Conditions should also satisfy the following expression:  
 $I_D V_D < (T_J - T_L) / R_{TH} j-I$

**OIP<sub>3</sub> vs. Frequency**  
V<sub>D</sub> = 4.9 V, I<sub>D</sub> = 80 mA



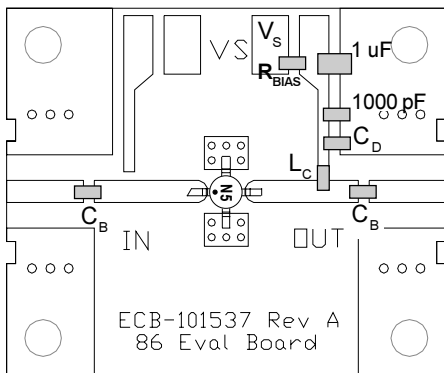
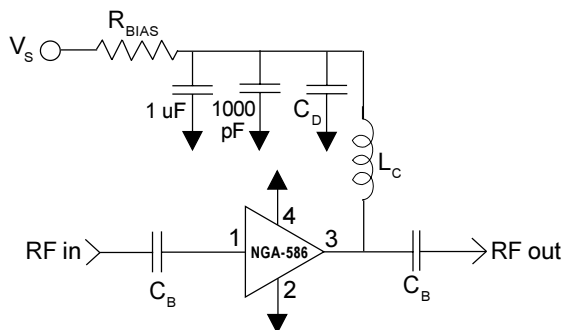
**P<sub>1dB</sub> vs. Frequency**  
V<sub>D</sub> = 4.9 v, I<sub>D</sub> = 80 mA





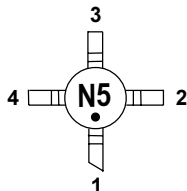
\* Note: In the applications circuit on page 4,  $R_{BIAS}$  compensates for voltage and current variation over temperature.

### Basic Application Circuit



### Part Identification Marking

The part will be marked with an "N5" designator on the top surface of the package.



### Caution: ESD sensitive

Appropriate precautions in handling, packaging and testing devices must be observed.

### Application Circuit Element Values

| Reference Designator | Frequency (Mhz) |        |       |       |       |
|----------------------|-----------------|--------|-------|-------|-------|
|                      | 500             | 850    | 1950  | 2400  | 3500  |
| C <sub>B</sub>       | 220 pF          | 100 pF | 68 pF | 56 pF | 39 pF |
| C <sub>D</sub>       | 100 pF          | 68 pF  | 22 pF | 22 pF | 15 pF |
| L <sub>C</sub>       | 68 nH           | 33 nH  | 22 nH | 18 nH | 15 nH |

### Recommended Bias Resistor Values for I<sub>D</sub>=80mA

$$R_{BIAS} = (V_S - V_D) / I_D$$

| Supply Voltage(V <sub>S</sub> ) | 7.5 V | 8 V  | 10 V | 12 V |
|---------------------------------|-------|------|------|------|
| R <sub>BIAS</sub>               | 33 Ω  | 39 Ω | 62 Ω | 91 Ω |

Note: R<sub>BIAS</sub> provides DC bias stability over temperature.

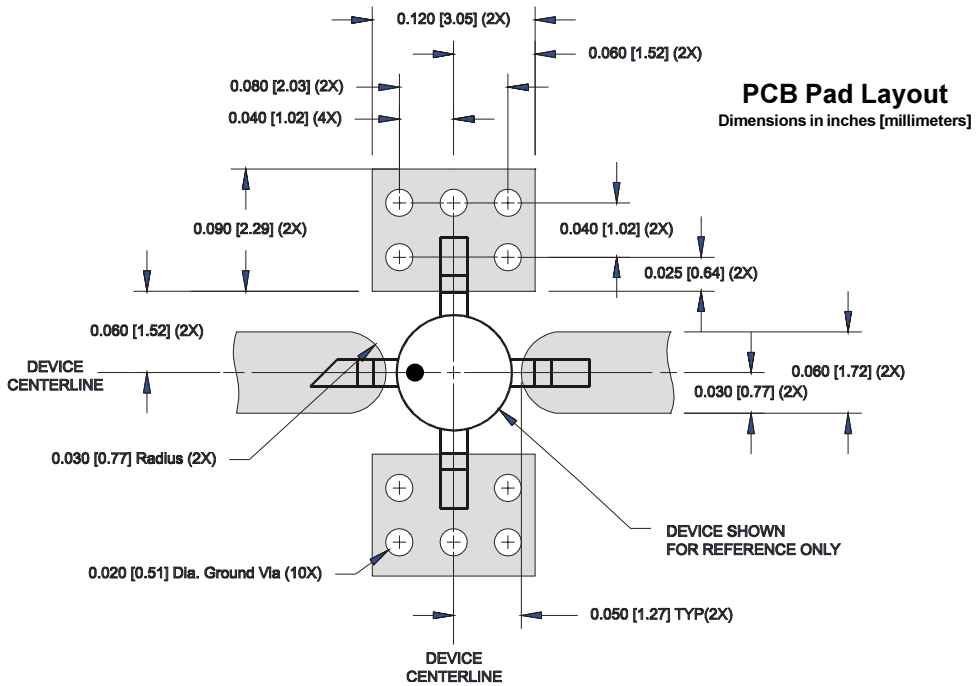
### Mounting Instructions

1. Use a large ground pad area under device pins 2 and 4 with many plated through-holes as shown.
2. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

| Pin # | Function    | Description   |
|-------|-------------|---|
| 1     | RF IN       | RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.             |
| 2, 4  | GND         | Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.        |
| 3     | RF OUT/BIAS | RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation. |

### Part Number Ordering Information

| Part Number | Reel Size | Devices/Reel |
|-------------|-----------|--------------|
| NGA-586     | 7"        | 1000         |



### Nominal Package Dimensions

Dimensions in inches [millimeters]  
 Refer to drawing posted at [www.sirenza.com](http://www.sirenza.com) for tolerances.

